

ISC Silicon NPN Power Transistor

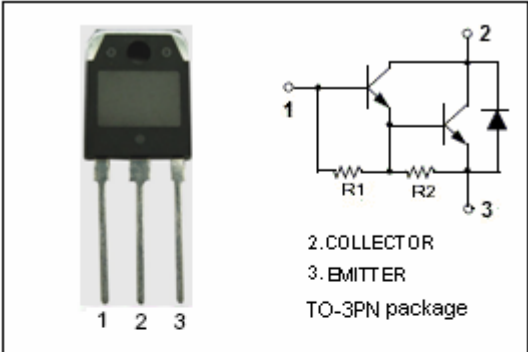
BU932P

DESCRIPTION

- High Voltage
- DARLINGTON

APPLICATIONS

- High ruggedness electronic ignitions.
- High voltage ignition coil driver

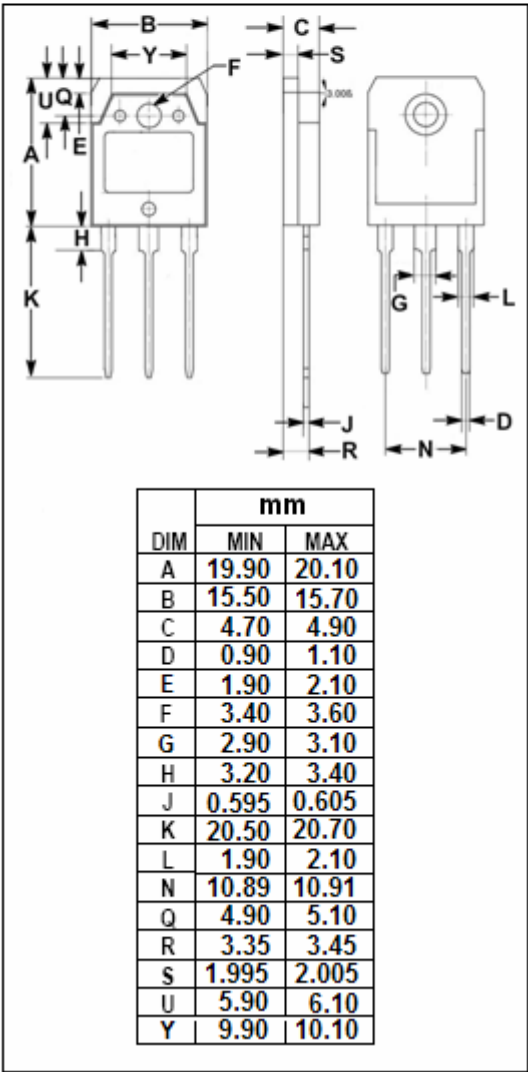


ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	500	V
V _{CEO}	Collector-Emitter Voltage	450	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	15	A
I _{CM}	Collector Current-peak	30	A
I _B	Base Current	1	A
I _{BM}	Base Current-peak	5	A
P _C	Collector Power Dissipation @T _C =25°C	105	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-40~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	2.08	°C/W



ISC Silicon NPN Power Transistor**BU932P****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 0.1A; I _B = 0	450			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 8A; I _B = 150mA			1.8	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 8A; I _B = 150mA			2.2	V
I _{CES}	Collector Cutoff Current	V _{CE} = 500V; V _{BE} = 0 V _{CE} = 500V; V _{BE} = 0; T _J = 125°C			1.0 5.0	mA
I _{CEO}	Collector Cutoff Current	V _{CE} = 450V; I _B = 0			1.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			50	mA
h _{FE}	DC Current Gain	I _C = 5A ; V _{CE} = 10V	300			
V _{ECF}	C-E Diode Forward Voltage	I _F = 10A			2.8	V